

IN THE CLAIMS:

Please amend claims 1 and 8 as follows.

a 1. (Amended) A semiconductor device comprising:

b metal interconnects made from a multi-layer film composed of a first metal film deposited on a semiconductor substrate with an insulating film sandwiched therebetween and a second metal film deposited on said first metal film, wherein the second metal film is a seed layer
c an interlayer insulating film fanned on said metal interconnects; and
a plug made from a third metal film selectively grown on said second metal film within a via hole formed in said interlayer insulating film.

a² 8. (Amended) A method for fabricating a semiconductor device comprising the

c^{mt} steps of:

depositing a first metal film on a semiconductor substrate with an insulating film sandwiched therebetween;

depositing a second metal film on said first metal film, wherein the second metal film is a seed layer;

forming an interlayer insulating film on said second metal film;

forming a via hole in said interlayer insulating film so as to expose said second metal film within said via hole;

forming a plug of a third metal film selectively grown on said second metal film

a²
cnt within said via hole;

forming a patterned interlayer insulating film by patterning said interlayer insulating film into the shape of interconnects; and

forming metal interconnects from a multi-layer film composed of said first metal film and said second metal film by etching said multi-layer film with said plug and said patterned interlayer insulating film used as a mask.
